

AMENDMENTS TO THE CLAIMS:

Kindly amend claims 1 and 8-10, and add new claim 17 as shown below.

This listing of claims will replace all prior versions and listings of claims in the
Application:

Claim 1 (currently amended): A semiconductor laser device comprising:

a heat radiating block;

one or more first semiconductor laser element(s) arranged on said heat radiating block
in a manner where one electrode is in direct physical contact therewith; and

one or more second semiconductor laser element(s) arranged on said heat radiating
block in an electrically insulated manner via a dielectric layer.

Claim 2 (original): The semiconductor laser device as set forth in Claim 1, wherein
said first and second semiconductor laser elements are both integrated into one chip,
and one electrode of the first semiconductor laser element is in contact with said block, and the
second semiconductor laser element is provided on said dielectric layer.

Claim 3 (original): The semiconductor laser device as set forth in Claim 1, wherein
said heat radiating block is an electrical conductor or a semiconductor.

Claim 4 (original): The semiconductor laser device as set forth in Claim 2, wherein
said heat radiating block is an electrical conductor or a semiconductor.

Claim 5 (original): The semiconductor laser device as set forth in Claim 1,
comprising:

a light output monitoring photodiode built onto said heat radiating block.

Claim 6 (original): The semiconductor laser device as set forth in Claim 2,
comprising:

a light output monitoring photodiode built onto said heat radiating block.

Claim 7 (original): The semiconductor laser device as set forth in Claim 3,
comprising:

a light output monitoring photodiode built onto said heat radiating block.

Claim 8 (currently amended): The semiconductor laser device as set forth in Claim 1,
wherein

said dielectric layer is formed of [[one]] a material selected from a group consisting of
silicon oxide, silicon nitride, titanium oxide, aluminum oxide, and aluminum nitride.

Claim 9 (currently amended): The semiconductor laser device as set forth in Claim 2,
wherein

said dielectric layer is formed of [[one]] a material selected from a group consisting of
silicon oxide, silicon nitride, titanium oxide, aluminum oxide, and aluminum nitride.

Claim 10 (currently amended): The semiconductor laser device as set forth in Claim
3, wherein

said dielectric layer is formed of [[one]] a material selected from a group consisting of
silicon oxide, silicon nitride, titanium oxide, aluminum oxide, and aluminum nitride.

Claim 11 (original): The semiconductor laser device as set forth in Claim 1, wherein
said first semiconductor laser element is greater in heat generation during driving or
smaller in heat radiation from an element exposed surface than said second semiconductor laser
element.

Claim 12 (original): The semiconductor laser device as set forth in Claim 2, wherein

said first semiconductor laser element is greater in heat generation during driving or smaller in heat radiation from an element exposed surface than said second semiconductor laser element.

Claim 13 (original): The semiconductor laser device as set forth in Claim 3, wherein said first semiconductor laser element is greater in heat generation during driving or smaller in heat radiation from an element exposed surface than said second semiconductor laser element.

Claim 14 (original): The semiconductor laser device as set forth in Claim 1, wherein said first semiconductor laser element is a semiconductor laser to emit a laser beam with a 650nm-band wavelength, and said second semiconductor laser element is a semiconductor laser to emit a laser beam with a 780nm-band wavelength.

Claim 15 (original): The semiconductor laser device as set forth in Claim 2, wherein said first semiconductor laser element is a semiconductor laser to emit a laser beam with a 650nm-band wavelength, and said second semiconductor laser element is a semiconductor laser to emit a laser beam with a 780nm-band wavelength.

Claim 16 (original): The semiconductor laser device as set forth in Claim 3, wherein said first semiconductor laser element is a semiconductor laser to emit a laser beam with a 650nm-band wavelength, and said second semiconductor laser element is a semiconductor laser to emit a laser beam with a 780nm-band wavelength.

Claim 17 (new): A semiconductor laser device comprising:

a semiconductor substrate;

a first semiconductor laser element directly provided on a said semiconductor substrate;

a second semiconductor laser element provided on a dielectric layer formed on said semiconductor substrate, said second semiconductor laser element being smaller in heat generation during driving; and

a photodiode provided on the surface of said semiconductor substrate for monitoring laser output from said first semiconductor laser element or said second semiconductor laser element, wherein said first semiconductor laser element and said photodiode are electrically insulated by a pn structure formed on the surface of said semiconductor substrate.

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